

# PH2731-80M Microwave Pulsed Power Transistor

## Design Characteristics

- 100  $\mu$ S Pulse Operation
- Broadband 2.7 - 3.1 GHz Operation
- Common Base Configuration
- Hermetic Metal / Ceramic Package
- Gold Metallization System

## Electrical Performance

$P_{OUT} = 80$  Watts

Gain > 8.0 dB

Efficiency > 40%

Input Return Loss > 9 dB

3:1 Output VSWR Ruggedness

Test Conditions: Broadband Test Fixture

Frequency = 2.7, 2.9, 3.1 GHz

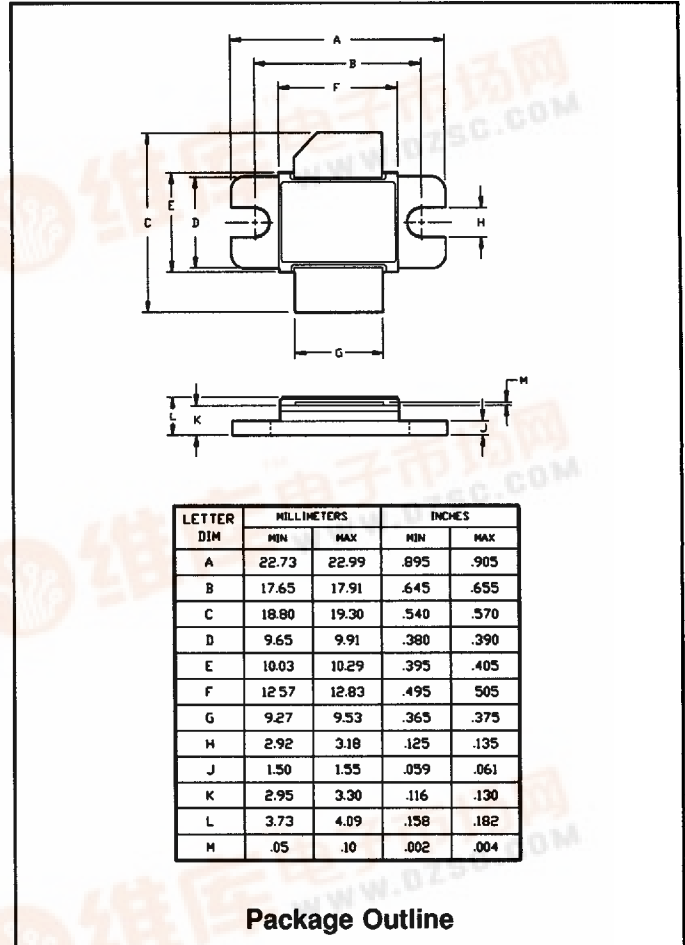
Vcc = 36 Volts

Pulse Width = 100  $\mu$ S

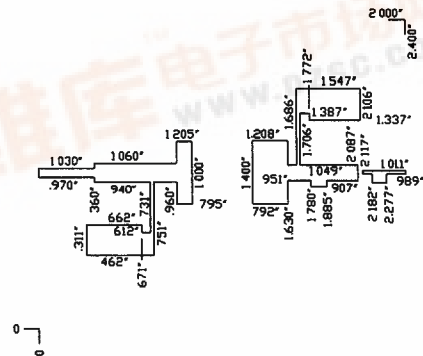
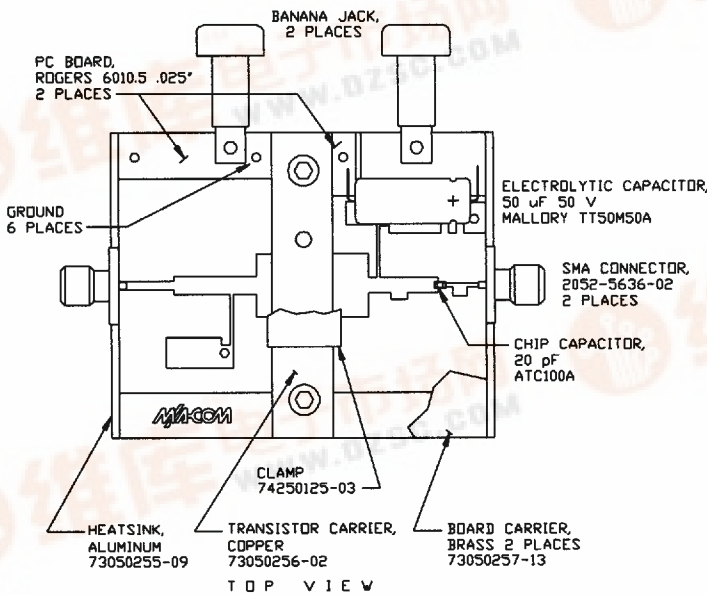
Duty Factor = 10%

Flange Temperature = 30°C

Fixture Impedance:	Freq (GHz)	Zif ( $\Omega$ )	Zof ( $\Omega$ )
	2.7	6.4 - j8.7	3.0 - j4.1
	2.9	6.0 - j7.9	2.9 - j3.5
	3.1	5.8 - j7.2	2.7 - j3.2



Package Outline



CIRCUIT DIMENSIONS  
MASK 75052731-80M

## Broadband Test Fixture

